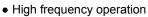


Schottky Diodes





- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260°C



Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

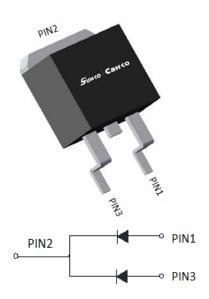
• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating -

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Polarity: As marked



■Maximum Ratings (Ta=25°C Unless otherwise specified)

= maximum (vatings (1a 25 0 0 most out of most opposited)				
PARAMETER	SYMBOL	UNIT	MBRBL2045CT	
Device marking code			MBRBL2045CT	
Repetitive Peak Reverse Voltage	V_{RRM}	V	45	
Average Rectified Output Current @60Hz sine wave, R-load, Ta (FIG 1)	I _o	А	20	
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	I _{FSM}	А	180	
Current Squared Time @1ms≤t≤8.3ms Tj=25℃,rating of per diode	l ² t	A ² s	134	
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ + 150	
Junction Temperature	Tj	°C	-55 ~ +150	

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL2045CT
Maximum instantaneous forward voltage drop per diode	V_{FM}	>	I _{FM} =10.0A	0.55
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _{RRM} Ta=25℃	0.2
	I _{RRM2}		V _{RM} =V _{RRM} Ta=100°C	50

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

P	ARAMETER	SYMBOL	UNIT	MBRBL2045CT
Thermal Resistance	Between junction and case	$R_{ heta J ext{-}C}$	°C/W	2.0



■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRBL2045CT	Approximate 1.43	50	2000	8000	Tube
MBRBL2045CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

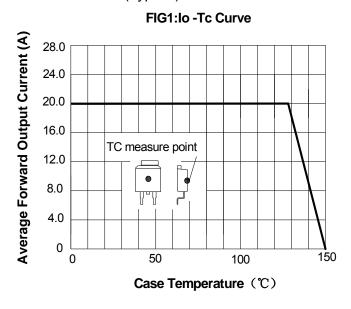
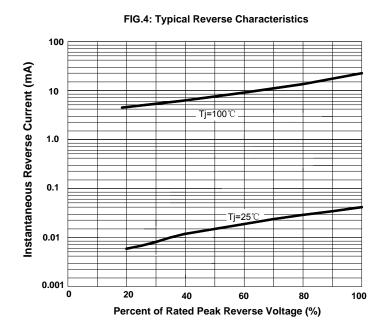
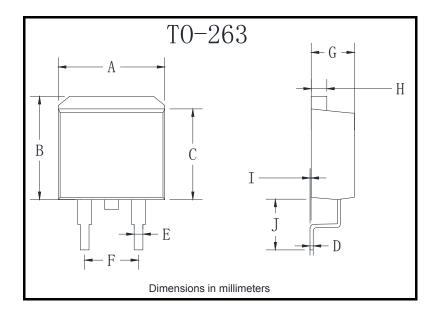


FIG2:Surge Forward Current Capability 180 Peak Forward Surge Current (A) 150 8.3ms Single 120 Half Sine-Wave JEDEC Method 90 60 30 0 2 5 10 20 50 100 **Number of Cycles**





■Outline Dimensions



TO-263					
Dim	Min	Max			
Α	9.5	11.5			
В	9.7	10.5			
С	8.4	9.0			
D	0.28	0.64			
E	0.68	0.94			
F	4.55	5.6			
G	4.04	5.10			
Н	1.14	1.4			
I	0	0.2			
J	4.9	6.05			



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